Supporting Information

Phonon scattering and electron doping by 2D structural defects in In:ZnO

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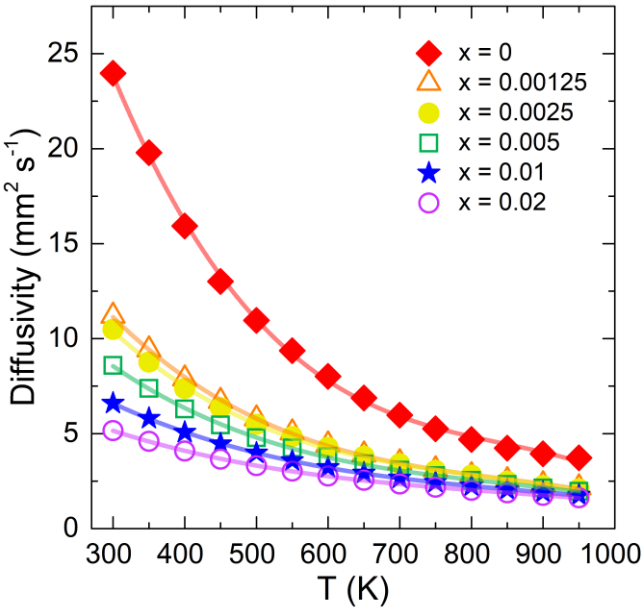

Figure S1. Temperature dependence of the thermal diffusivity in the $Zn_{1-x}In_xO$ series.

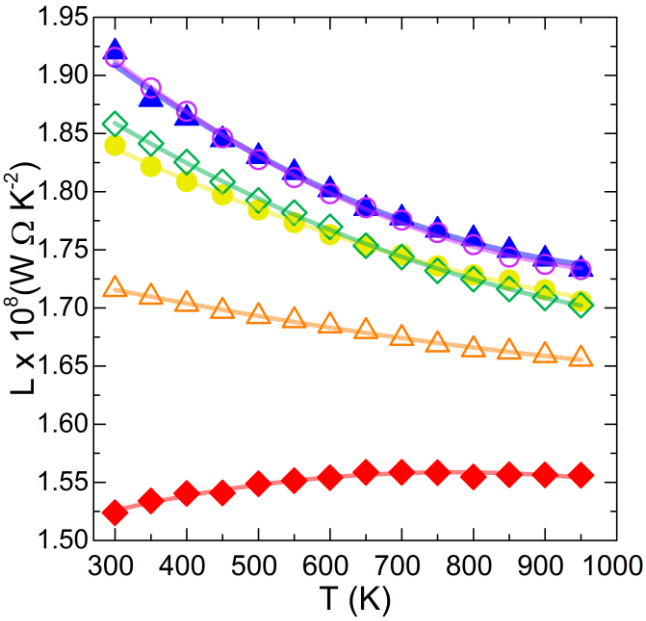

Figure S2. Lorentz number as function of temperature.[46]

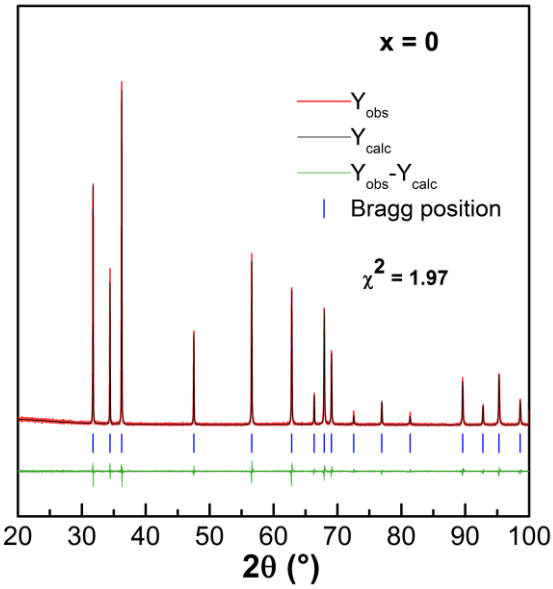

Figure S3. Pattern matching refinement of the XRD pattern for the *x* = 0 sample.

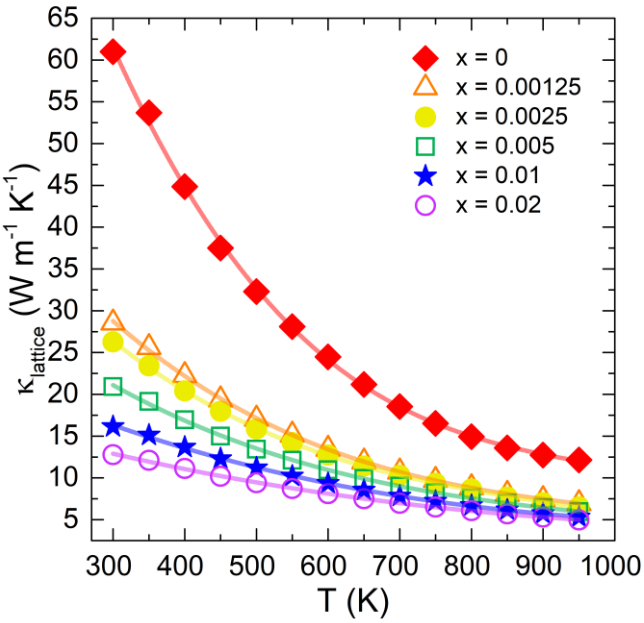

Figure S4. Temperature dependence of the lattice thermal conductivity in the $Zn_{1-x}In_xO$ series.

Table S1. Relative densities in the $Zn_{1-x}In_xO$ series.

	$x = 0$	$x = 0.00125$	$x = 0.0025$	$x = 0.005$	$x = 0.01$	$x = 0.02$
RD	91.4%	91.8%	90.4%	87.9%	88.4%	89.7%

Table S2. Cp values versus temperature (See reference 45).

T (K)	Cp (J/g K)
300	0.497
350	0.53
400	0.55
450	0.563
500	0.576
550	0.5865
600	0.597
650	0.602
700	0.607
750	0.615
800	0.623
850	0.628
900	0.633
950	0.638